

AMENDMENTS TO THE ABSTRACT

Please replace the original Abstract with the following new Abstract.

ABSTRACT

A charge sensing device with a sense amplifier system which can be implemented in a non-volatile matrix-addressable memory device comprising an electrical polarizable dielectric memory material exhibiting hysteresis, particularly a ferroelectric or electret material. The memory cells of the memory device can be selectively addressed for a write/read operation and the sense amplifier system is used for readout of polarization states of the memory cells.